WM2HA020120K

V_{DS}	=	1200	V
$R_{DS(on)}$	=	20	P
I_D@25	=	100	A

N-Channel SiC Power MOSFET

G2 MOSFET Technology

Features

- High Blocking Voltage with Low On

Package

Typical Performance

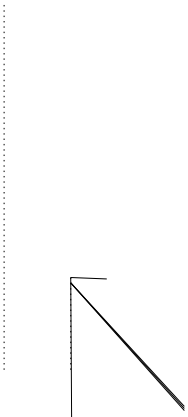


Figure 1. Output Characteristics T_J = -55

Figure 2. Output Characteristics T_J = 25

Figure 3. Output Characteristics T_J = 175

Figure 4. Normalized On-Resistance vs. Temperature

Figure 5. On-Resistance vs. Drain Current For Various Temperatures

Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

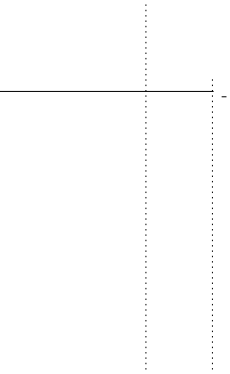


Figure 13. 3rd Quadrant Characteristic at -55

Figure 14. 3rd Quadrant Characteristic at 25

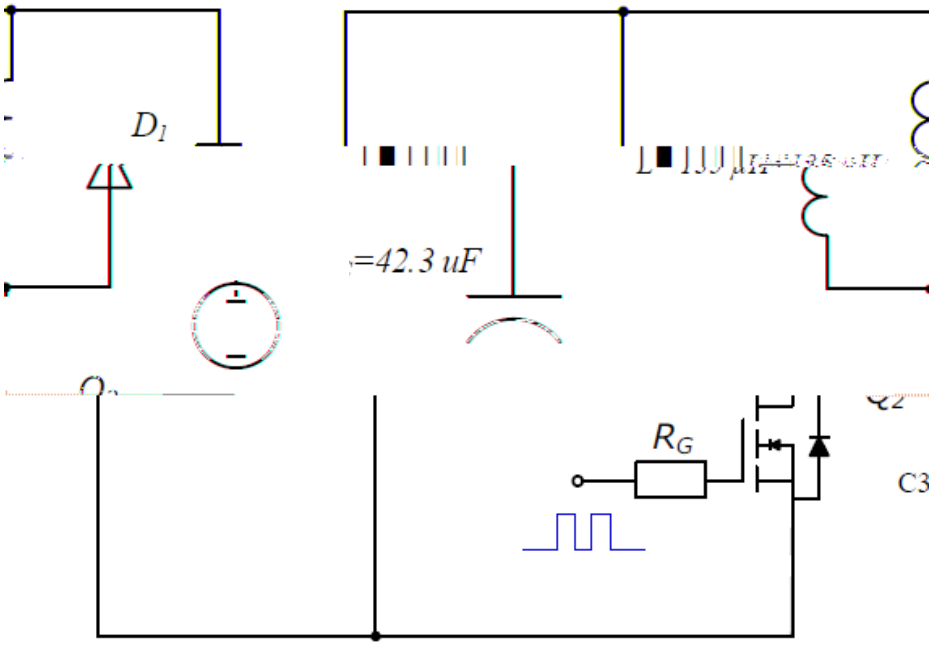
Figure 15. 3rd Quadrant Characteristic at 175

Figure 16. Output Capacitor Stored Energy

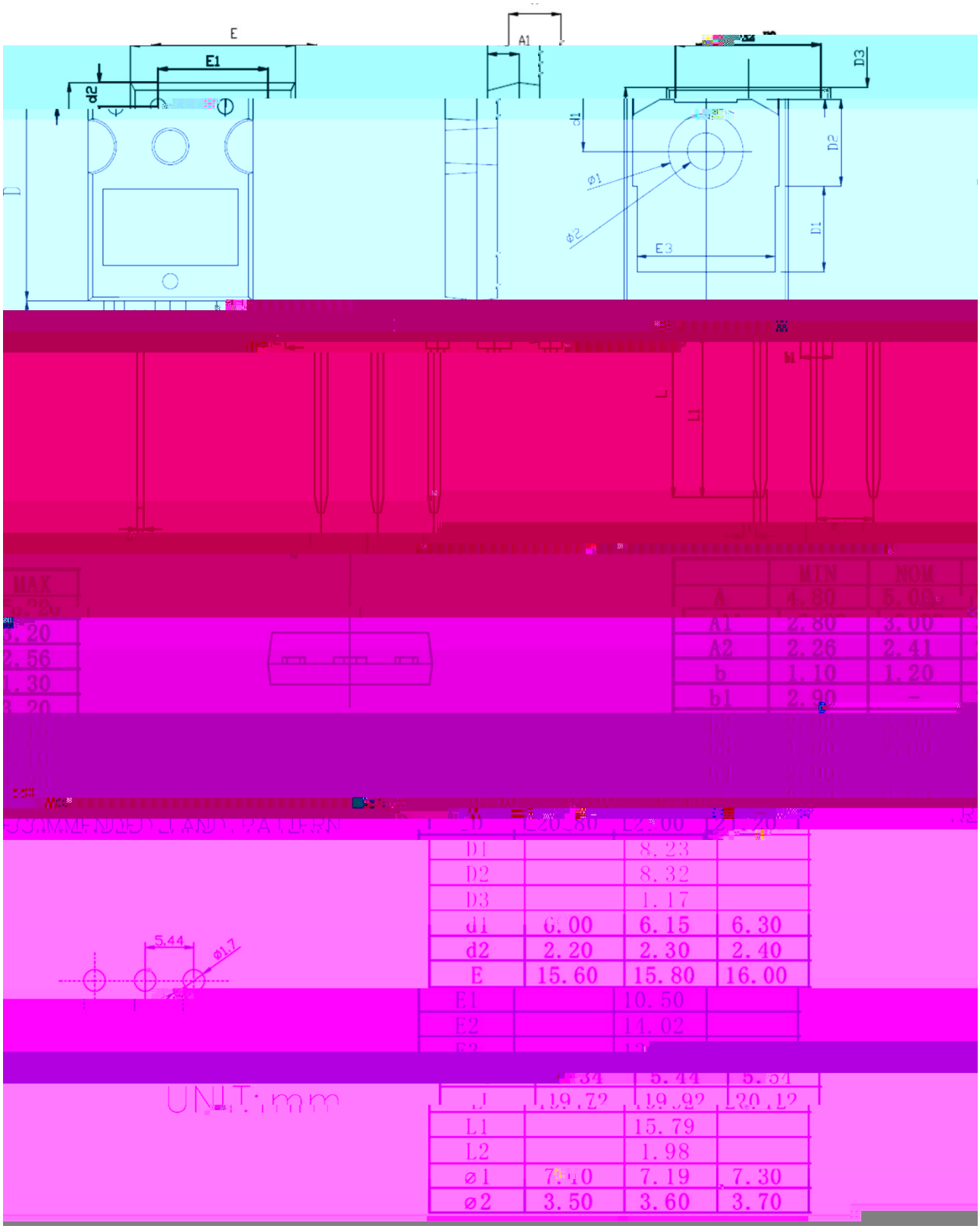
Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1200V)

Test Circuit Schematic



Package Dimensions



Notes

1) Before using our products, please couyhengf0ea0 g /TT0 8u.5 (13.6 (o3 (t (k)-2.7 (ee)13.i ( )6.7 (i (13.6 (onage3 (ef)2e)13.4 (T0 8u.5

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